

11/18/02

PATENT
Docket No. 150.00560104**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): Lee et al.) Group Art Unit: 1765
Serial No.: 10/050,639) Examiner: D. Deo
Confirmation No.: 6476)
Filed: 15 January 2002)
For: **METHOD AND COMPOSITION FOR SELECTIVELY ETCHING AGAINST
COBALT SILICIDE**

AMENDMENT AND RESPONSE
UNDER 37 C.F.R. § 1.116

Assistant Commissioner for Patents
BOX AF
Washington D.C. 20231

Dear Sir:

In response to the Final Office Action dated 6 September 2002, please amend the above-identified application as follows:

In the Claims

Please add new claims 76-88; amend claims 46, 51, 53, and 55; and cancel claims 47-50. Per 37 C.F.R. § 1.121, amended claims are also shown in Appendix A with notations to indicate changes made (for convenience, all pending claims, including those added hereby, are provided in Appendix A).

46. **(Once Amended)** An etching method for use in integrated circuit fabrication, the method comprising:

providing a substrate assembly comprising a metal nitride region and a cobalt silicide region; and

selectively etching a portion of the metal nitride region against the cobalt silicide region using a solution comprising a mineral acid and a peroxide, wherein the solution etches the